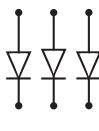




CMKSH2-4LR

SURFACE MOUNT ULTRAmini™  
TRIPLE ISOLATED SILICON  
LOW V<sub>F</sub> SCHOTTKY DIODES

ULTRAmini™



SOT-363 CASE

**Central**<sup>TM</sup>  
**Semiconductor Corp.****DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMKSH2-4LR contains three (3) Isolated Silicon Low V<sub>F</sub> Schottky Diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmini™ device has been designed for switching applications requiring a low forward voltage drop.

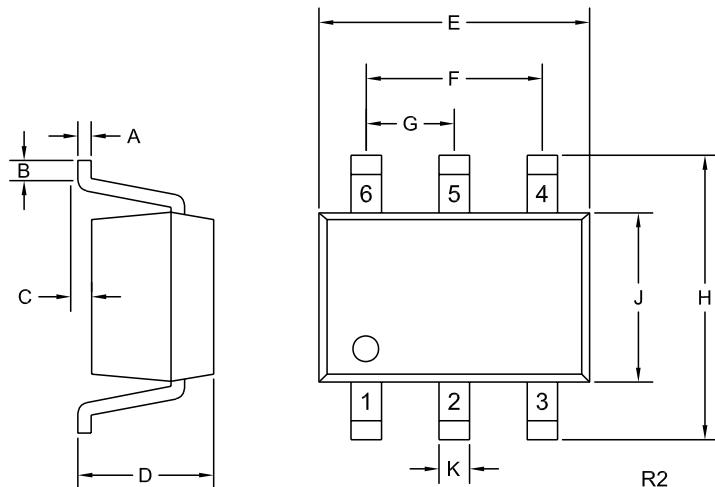
**MARKING CODE: CHTL****MAXIMUM RATINGS: (T<sub>A</sub>=25°C)**

	SYMBOL	UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	V
Continuous Forward Current	I <sub>F</sub>	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	mA
Forward Surge Current, t <sub>p</sub> =10ms	I <sub>FSM</sub>	A
Power Dissipation	P <sub>D</sub>	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	°C
Thermal Resistance	Θ <sub>JA</sub>	°C/W

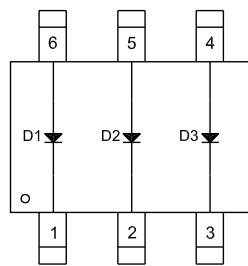
**ELECTRICAL CHARACTERISTICS PER DIODE: (T<sub>A</sub>=25°C unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =20V		11	50	µA
BV <sub>R</sub>	I <sub>R</sub> =100µA	40	53		V
V <sub>F</sub>	I <sub>F</sub> =10mA		0.24	0.325	V
V <sub>F</sub>	I <sub>F</sub> =100mA		0.35	0.40	V
V <sub>F</sub>	I <sub>F</sub> =200mA		0.42	0.50	V
C <sub>T</sub>	V <sub>R</sub> =4.0V, f=1.0MHz		8.5	10	pF
t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =1.0mA, R <sub>L</sub> =100Ω		4.0	5.0	ns

SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) CATHODE D1
- 2) CATHODE D2
- 3) CATHODE D3
- 4) ANODE D3
- 5) ANODE D2
- 6) ANODE D1

MARKING CODE: CHTL

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R1 (21-November 2008)